

# Frank Bertram

## List of Publications by Year in descending order

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197  
papers

5,579  
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125106

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104191

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201  
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201  
docs citations

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times ranked

5937  
citing authors

#	ARTICLE	IF	CITATIONS
1	Desorption induced formation of low-density GaN quantum dots: nanoscale correlation of structural and optical properties. <i>Journal Physics D: Applied Physics</i> , 2022, 55, 145102.	1.3	0
2	Direct Imaging of the Carrier Capture into Individual InP Quantum Dots of a Semiconductor Disk Laser Membrane. <i>ACS Nano</i> , 2022, 16, 4619-4628.	7.3	0
3	Correlating yellow and blue luminescence with carbon doping in GaN. <i>Journal of Crystal Growth</i> , 2022, 586, 126634.	0.7	2
4	Color-tunable 3D InGaN/GaN Multi-Quantum-Well Light-Emitting Diode Based on Microfacet Emission and Programmable Driving Power Supply. <i>Advanced Optical Materials</i> , 2021, 9, .	3.6	14
5	Characteristic emission from quantum dot-like intersection nodes of dislocations in GaN. <i>Journal of Physics: Conference Series</i> , 2021, 1851, 012013.	0.3	1
6	Demonstration of lateral epitaxial growth of AlN on Si (1 1 1) at low temperatures by pulsed reactive sputter epitaxy. <i>Journal of Crystal Growth</i> , 2021, 571, 126250.	0.7	6
7	Cathodoluminescence nano-characterization of individual GaN/AlN quantum disks embedded in nanowires. <i>Applied Physics Letters</i> , 2020, 117, 133106.	1.5	3
8	Thermally annealed wafer-scale h-BN films grown on sapphire substrate by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2020, 116, .	1.5	16
9	Optical and Structural Properties of Nitride Based Nanostructures. <i>Springer Series in Solid-state Sciences</i> , 2020, , 135-201.	0.3	2
10	Individually resolved luminescence from closely stacked GaN/AlN quantum wells. <i>Photonics Research</i> , 2020, 8, 610.	3.4	8
11	Nitride Microcavities and Single Quantum Dots for Classical and Non-classical Light Emitters. <i>Springer Series in Solid-state Sciences</i> , 2020, , 453-504.	0.3	1
12	Ordered arrays of defect-free GaN nanocolumns with very narrow excitonic emission line width. <i>Journal of Crystal Growth</i> , 2019, 525, 125189.	0.7	7
13	Intensive luminescence from a thick, indium-rich In <sub>0.7</sub> Ga <sub>0.3</sub> N film. <i>Japanese Journal of Applied Physics</i> , 2019, 58, 065503.	0.8	2
14	Nanoscale mapping of carrier recombination in GaAs/AlGaAs core-multishell nanowires by cathodoluminescence imaging in a scanning transmission electron microscope. <i>Applied Physics Letters</i> , 2019, 115, 243102.	1.5	4
15	Surface development of a brazing alloy during heat treatment—a comparison between UHV and APXPS. <i>Journal of Physics Condensed Matter</i> , 2018, 30, 024004.	0.7	2
16	Direct imaging of Indium-rich triangular nanoprisms self-organized formed at the edges of InGaN/GaN core-shell nanorods. <i>Scientific Reports</i> , 2018, 8, 16026.	1.6	19
17	MOVPE-growth of InGaSb/AlP/GaP(001) Quantum Dots for Nanoscale Memory Applications. <i>Physica Status Solidi (B): Basic Research</i> , 2018, 255, 1800182.	0.7	24
18	Recent progress in nonpolar and semi-polar GaN light emitters on patterned Si substrates. , 2018, , .		3

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19	Compositionally graded InGaN layers grown on vicinal N-face GaN substrates by plasma-assisted molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2017, 465, 55-59.	0.7	16
20	Theoretical study of time-resolved luminescence in semiconductors. IV. Lateral inhomogeneities. <i>Journal of Applied Physics</i> , 2017, 121, .	1.1	11
21	Emission of Linearly Polarized Single Photons from Quantum Dots Contained in Nonpolar, Semipolar, and Polar Sections of Pencil-Like InGaN/GaN Nanowires. <i>ACS Photonics</i> , 2017, 4, 657-664.	3.2	44
22	Exciton emission of quasi-2D InGaN in GaN matrix grown by molecular beam epitaxy. <i>Scientific Reports</i> , 2017, 7, 46420.	1.6	14
23	Selective area growth of AlN/GaN nanocolumns on (0001) and (11 $\bar{2}$ ) GaN/sapphire for semi-polar and non-polar AlN pseudo-templates. <i>Nanotechnology</i> , 2017, 28, 365704.	1.3	6
24	Nanometer-scale Resolved Cathodoluminescence Imaging: New Insights into GaAs/AlGaAs Core-shell Nanowire Lasers. <i>Microscopy and Microanalysis</i> , 2017, 23, 1470-1471.	0.2	0
25	Surface development of an aluminum brazing sheet during heating studied by XPEEM and XPS. <i>Materials Research Express</i> , 2016, 3, 106506.	0.8	5
26	Improvement of optical quality of semipolar (112 $\bar{2}$ ) GaN on <i>m</i> -plane sapphire by <i>in-situ</i> epitaxial lateral overgrowth. <i>Journal of Applied Physics</i> , 2016, 119, .	1.1	12
27	Direct correlations of structural and optical properties of three-dimensional GaN/InGaN core/shell micro-light emitting diodes. <i>Japanese Journal of Applied Physics</i> , 2016, 55, 05FJ09.	0.8	22
28	Nanoscale Insights into InGaN/GaN Core-Shell Nanorods: Structure, Composition, and Luminescence. <i>Nano Letters</i> , 2016, 16, 5340-5346.	4.5	43
29	Embedded GaN nanostripes on <i>c</i> -sapphire for DFB lasers with semipolar quantum wells. <i>Physica Status Solidi (B): Basic Research</i> , 2016, 253, 180-185.	0.7	5
30	Defect reduced selectively grown GaN pyramids as template for green InGaN quantum wells. <i>Physica Status Solidi (B): Basic Research</i> , 2016, 253, 67-72.	0.7	2
31	Polarization engineering of <i>c</i> -plane InGaN quantum wells by pulsed-flow growth of AlInGaN barriers. <i>Physica Status Solidi (B): Basic Research</i> , 2016, 253, 118-125.	0.7	6
32	Nanoscale cathodoluminescence of stacking faults and partial dislocations in <i>a</i> -plane GaN. <i>Physica Status Solidi (B): Basic Research</i> , 2016, 253, 73-77.	0.7	2
33	Direct microscopic correlation of real structure and optical properties of semipolar GaN based on pre-patterned <i>r</i> -plane sapphire. <i>Physica Status Solidi (B): Basic Research</i> , 2016, 253, 54-60.	0.7	1
34	Nanoscale cathodoluminescence imaging of III $\bar{c}$ -nitride-based LEDs with semipolar quantum wells in a scanning transmission electron microscope. <i>Physica Status Solidi (B): Basic Research</i> , 2016, 253, 112-117.	0.7	7
35	Microscopic nature of crystal phase quantum dots in ultrathin GaAs nanowires by nanoscale luminescence characterization. <i>New Journal of Physics</i> , 2016, 18, 063009.	1.2	12
36	Influence of composition, strain, and electric field anisotropy on different emission colors and recombination dynamics from InGaN nanodisks in pencil-like GaN nanowires. <i>Physical Review B</i> , 2016, 93, .	1.1	18

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37	Structural and optical nanoscale analysis of GaN core-shell microrod arrays fabricated by combined top-down and bottom-up process on Si(111). Japanese Journal of Applied Physics, 2016, 55, 05FF02.	0.8	4
38	Clustered quantum dots in single GaN islands formed at threading dislocations. Japanese Journal of Applied Physics, 2016, 55, 05FF04.	0.8	5
39	Phosphor-converted white light from blue-emitting InGaN microrod LEDs. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 1577-1584.	0.8	48
40	Direct evidence of single quantum dot emission from GaN islands formed at threading dislocations using nanoscale cathodoluminescence: A source of single photons in the ultraviolet. Applied Physics Letters, 2015, 106, .	1.5	29
41	Determination of carrier diffusion length in GaN. Journal of Applied Physics, 2015, 117, .	1.1	33
42	STEM-CL investigations on the influence of stacking faults on the optical emission of cubic GaN epilayers and cubic GaN/AlN multi-quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2015, 12, 469-472.	0.8	18
43	Optical Emission of Individual GaN Nanocolumns Analyzed with High Spatial Resolution. Nano Letters, 2015, 15, 5105-5109.	4.5	35
44	Enhancement of optical and structural quality of semipolar (11-22) GaN by introducing nanoporous SiNx interlayers. , 2015, , .		2
45	Indium-incorporation efficiency in semipolar (11-22) oriented InGaN-based light emitting diodes. , 2015, , .		6
46	The thickness of native oxides on aluminum alloys and single crystals. Applied Surface Science, 2015, 349, 826-832.	3.1	174
47	Ordered arrays of InGaN/GaN dot-in-a-wire nanostructures as single photon emitters. Proceedings of SPIE, 2015, , .	0.8	10
48	Strong exciton-photon coupling in hybrid InGaN-based microcavities on GaN substrates. Proceedings of SPIE, 2015, , .	0.8	0
49	Blue-to-green single photons from InGaN/GaN dot-in-a-nanowire ordered arrays. Europhysics Letters, 2015, 111, 24001.	0.7	24
50	Gallium gradients in Cu(In,Ga)Se <sub>2</sub> thin-film solar cells. Progress in Photovoltaics: Research and Applications, 2015, 23, 717-733.	4.4	122
51	Nanoscale Characterization of Structural and Optical Properties of Nitride Nanostructures Using Helium Temperature Scanning Electron Microscopy Cathodoluminescence. , 2014, , .		0
52	Advances in MBE Selective Area Growth of III-Nitride Nanostructures: From NanoLEDs to Pseudo Substrates. International Journal of High Speed Electronics and Systems, 2014, 23, 1450020.	0.3	4
53	Extended defects in GaN nanocolumns characterized by cathodoluminescence directly performed in a transmission electron microscope. Turkish Journal of Physics, 2014, 38, 323-327.	0.5	0
54	<i>In situ</i> anodization of aluminum surfaces studied by x-ray reflectivity and electrochemical impedance spectroscopy. Journal of Applied Physics, 2014, 116, .	1.1	17

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55	Determination of carrier diffusion length in p- and n-type GaN. , 2014, , .		3
56	Optical properties of <i>m</i> -plane GaN grown on patterned Si(112) substrates by MOCVD using a two-step approach. Proceedings of SPIE, 2014, , .	0.8	1
57	Impact of extended defects on optical properties of (1-101)GaN grown on patterned Si. Proceedings of SPIE, 2014, , .	0.8	1
58	Spatially resolved optical emission of cubic GaN/AlN multi-quantum well structures. Materials Research Society Symposia Proceedings, 2014, 1736, 25.	0.1	2
59	Growth of InGaN/GaN core-shell structures on selectively etched GaN rods by molecular beam epitaxy. Journal of Crystal Growth, 2014, 392, 5-10.	0.7	13
60	Symmetry dependent optoelectronic properties of grain boundaries in polycrystalline Cu(In,Ga)Se <sub>2</sub> thin films. Journal of Applied Physics, 2014, 115, 023514.	1.1	12
61	InGaN: Direct correlation of nanoscopic morphology features with optical and structural properties. Applied Physics Letters, 2014, 105, 072108.	1.5	6
62	Nano-scale luminescence characterization of individual InGaN/GaN quantum wells stacked in a microcavity using scanning transmission electron microscope cathodoluminescence. Applied Physics Letters, 2014, 105, 032101.	1.5	30
63	Group III nitride core-shell nano- and microrods for optoelectronic applications. Physica Status Solidi - Rapid Research Letters, 2013, 7, 800-814.	1.2	76
64	Investigation of vertical compositional gradients in Cu(In,Ga)Se <sub>2</sub> by highly spatially and spectrally resolved cathodoluminescence microscopy. Thin Solid Films, 2013, 535, 270-274.	0.8	9
65	Green to blue polarization compensated c-axis oriented multi-quantum wells by AlGaInN barrier layers. Applied Physics Letters, 2013, 102, .	1.5	13
66	Depth distribution of carrier lifetimes in semipolar (11̄01) GaN grown by MOCVD on patterned Si substrates. Proceedings of SPIE, 2013, , .	0.8	0
67	MOVPE growth of semi-polar GaN light-emitting diode structures on planar Si(112) and Si(113) substrates. Journal of Crystal Growth, 2013, 370, 288-292.	0.7	15
68	Optical studies of strain and defect distribution in semipolar (11̄01) GaN on patterned Si substrates. Journal of Applied Physics, 2013, 114, 113502.	1.1	25
69	GaN laser structure with semipolar quantum wells and embedded nanostripes. , 2013, , .		0
70	Microscopic distribution of extended defects and blockage of threading dislocations by stacking faults in semipolar (11̄01) GaN revealed from spatially resolved luminescence. Applied Physics Letters, 2013, 103, .	1.5	11
71	GaN-Based Vertical Cavities with All Dielectric Reflectors by Epitaxial Lateral Overgrowth. Japanese Journal of Applied Physics, 2013, 52, 08JH03.	0.8	6
72	An improved carrier rate model to evaluate internal quantum efficiency and analyze efficiency droop origin of InGaN based light-emitting diodes. Journal of Applied Physics, 2012, 112, 023107.	1.1	53

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73	Excitonic transport in ZnO. Proceedings of SPIE, 2012, , .	0.8	1
74	Direct nano-scale correlation of structural and optical properties of lattice matched AlInN/AlGaN DBRs using helium temperature scanning transmission electron microscopy cathodoluminescence. Microscopy and Microanalysis, 2012, 18, 1874-1875.	0.2	1
75	Direct imaging of GaN Pyramids covered by InGaN Single Quantum Well using nano-scale Scanning Transmission Electron Microscopy Cathodoluminescence. Microscopy and Microanalysis, 2012, 18, 1838-1839.	0.2	1
76	Highly spatially resolved Cathodoluminescence of Single GaN Quantum Dots directly performed in a Scanning Transmission Electron Microscope. Microscopy and Microanalysis, 2012, 18, 1878-1879.	0.2	2
77	Excitonic transport in ZnO. Journal of Materials Research, 2012, 27, 2225-2231.	1.2	21
78	Single-photon emission from electrically driven InP quantum dots epitaxially grown on CMOS-compatible Si(001). Nanotechnology, 2012, 23, 335201.	1.3	10
79	Effect of MOCVD growth conditions on the optical properties of semipolar (1-101) GaN on Si patterned substrates. Proceedings of SPIE, 2012, , .	0.8	4
80	Cathodoluminescence directly performed in a transmission electron microscope: nanoscale correlation of structural and optical properties. Microscopy and Microanalysis, 2012, 18, 1834-1835.	0.2	1
81	Semipolar GaInN quantum well structures on large area substrates. Physica Status Solidi (B): Basic Research, 2012, 249, 464-467.	0.7	7
82	Growth and stacking fault reduction in semi-polar GaN films on planar Si(112) and Si(113). Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 507-510.	0.8	16
83	Comprehensive Comparison of Various Techniques for the Analysis of Elemental Distributions in Thin Films. Microscopy and Microanalysis, 2011, 17, 728-751.	0.2	72
84	MOVPE of CuGaSe <sub>2</sub> on GaAs in the presence of a Cu <sub>x</sub> Se secondary phase. Journal of Crystal Growth, 2011, 315, 82-86.	0.7	14
85	Indium incorporation in GaInN/GaN quantum well structures on polar and nonpolar surfaces. Physica Status Solidi (B): Basic Research, 2011, 248, 600-604.	0.7	15
86	Growth and coalescence behavior of semipolar $(1\bar{1}\bar{2})$ GaN on pre-structured $c$ -plane sapphire substrates. Physica Status Solidi (B): Basic Research, 2011, 248, 588-593.	0.7	34
87	Three-dimensional GaN for semipolar light emitters. Physica Status Solidi (B): Basic Research, 2011, 248, 549-560.	0.7	62
88	High wavelength tunability of InGaN quantum wells grown on semipolar GaN pyramid facets. Physica Status Solidi (B): Basic Research, 2011, 248, 605-610.	0.7	21
89	Spectrally and time-resolved cathodoluminescence microscopy of semipolar InGaN SQW on $(1\bar{1}\bar{2})$ and $(10\bar{1})$ pyramid facets. Physica Status Solidi (B): Basic Research, 2011, 248, 632-637.	0.7	12
90	Spectral features in different sized InGaN/GaN micropylramids. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2387-2389.	0.8	2

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91	Epitaxial lateral overgrowth of non-polar GaN(111 $\bar{1}$ ,00) on Si(112) patterned substrates by MOCVD. Journal of Crystal Growth, 2011, 314, 129-135.	0.7	20
92	Anti-phase domains in cubic GaN. Journal of Applied Physics, 2011, 110, .	1.1	26
93	Eliminating stacking faults in semi-polar GaN by AlN interlayers. Applied Physics Letters, 2011, 99, 021905.	1.5	22
94	Optical properties of nonpolar (1-100) and semipolar (1-101)GaN grown by MOCVD on Si patterned substrates. Proceedings of SPIE, 2011, , .	0.8	5
95	Well width study of InGaN multiple quantum wells for blue-green emitter. Journal of Crystal Growth, 2010, 312, 3428-3433.	0.7	10
96	GaNN $\bar{c}$ -based LED structures on selectively grown semi-polar crystal facets. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1407-1413.	0.8	22
97	Semipolar GaInN/GaN light-emitting diodes grown on honeycomb patterned substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2140-2143.	0.8	27
98	Luminescence Properties of Photonic Crystal InGaN/GaN Light Emitting Layers on Silicon-on-Insulator. Electrochemical and Solid-State Letters, 2010, 13, H343.	2.2	6
99	Structure and luminescence of (Ca,Sr)2SiS4 $\hat{c}$ -phosphors. Journal Physics D: Applied Physics, 2010, 43, 085401.	1.3	29
100	AlInN/GaN based multi quantum well structures growth and optical properties. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S451.	0.8	11
101	MOVPE growth of high-quality Al $\bar{c}$ >0.1</sub>Ga<sub>0.9</sub>N on Si(111) substrates for UV LEDs. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S455.	0.8	3
102	Microstructural anisotropy of a-plane GaN analyzed by high resolution X-ray diffraction. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S498.	0.8	12
103	Fabrication and optical properties of C $\hat{c}$ -SiC/Si hybrid rolled-up microtubes. Journal of Applied Physics, 2009, 105, 016103.	1.1	13
104	Fabrication, Self-Assembly, and Properties of Ultrathin AlN/GaN Porous Crystalline Nanomembranes: Tubes, Spirals, and Curved Sheets. ACS Nano, 2009, 3, 1663-1668.	7.3	91
105	Analysis of point defects in AlN epilayers by cathodoluminescence spectroscopy. Applied Physics Letters, 2009, 95, .	1.5	28
106	Growth of QW structures with high indium concentration on -plane and -plane surfaces by MOVPE. Journal of Crystal Growth, 2008, 310, 4987-4991.	0.7	6
107	Microscopic recombination kinetics in high quality, fully coalesced a-plane GaN ELO structures investigated by ps-time-resolved cathodoluminescence microscopy. , 2008, , .		0
108	A -plane GaN epitaxial lateral overgrowth structures: Growth domains, morphological defects, and impurity incorporation directly imaged by cathodoluminescence microscopy. Applied Physics Letters, 2008, 92, .	1.5	35

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109	Time-resolved cathodoluminescence of Mg-doped GaN. Applied Physics Letters, 2008, 93, .	1.5	19
110	Effect of the growth temperature and the AlN mole fraction on In incorporation and properties of quaternary III-nitride layers grown by molecular beam epitaxy. Journal of Applied Physics, 2008, 104, 083510.	1.1	16
111	Metalorganic vapor phase epitaxy of ZnO: towards p-type conductivity. , 2007, 6474, 32.		9
112	Thin film growth of ZnO and its relation to substrate properties. , 2007, , .		0
113	Complex excitonic recombination kinetics in ZnO: Capture, relaxation, and recombination from steady state. Applied Physics Letters, 2007, 90, 041917.	1.5	31
114	Blue light emitting diodes on Si(001) grown by MOVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 41-44.	0.8	4
115	Laser-Interference Lithography Tailored for Highly Symmetrically Arranged ZnO Nanowire Arrays. Small, 2007, 3, 76-80.	5.2	95
116	Homoepitaxy of ZnO: from the substrates to doping. Physica Status Solidi (B): Basic Research, 2007, 244, 1451-1457.	0.7	23
117	Vapour transport growth of ZnO nanorods. Applied Physics A: Materials Science and Processing, 2007, 88, 17-20.	1.1	16
118	Direct imaging of phase separation in ZnCdO layers. Applied Physics Letters, 2006, 88, 061915.	1.5	55
119	Catalyst-free vapor-phase transport growth of vertically aligned ZnO nanorods on 6H-SiC and (11-20)Al <sub>2</sub> O <sub>3</sub> . Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1046-1050.	0.8	35
120	MBE growth of ZnO layers on sapphire employing hydrogen peroxide as an oxidant. Journal of Crystal Growth, 2006, 287, 7-11.	0.7	39
121	MOVPE growth of high-quality AlN. Journal of Crystal Growth, 2006, 297, 306-310.	0.7	68
122	Growth and Characterization of Homoepitaxial ZnO Thin Films Grown by CVD. Materials Research Society Symposia Proceedings, 2006, 957, 1.	0.1	0
123	Microscopic Luminescence Properties of ZnO and ZnO Based Heterostructures. Acta Physica Polonica A, 2006, 110, 103-110.	0.2	1
124	ZnO MOVPE growth: From local impurity incorporation towards p-type doping. Superlattices and Microstructures, 2005, 38, 245-255.	1.4	27
125	Localization versus carrier-screening effects in InGaN quantum wells â€” A time-resolved cathodoluminescence study. AIP Conference Proceedings, 2005, , .	0.3	1
126	Local luminescence of ZnO nanowire-covered surface: A cathodoluminescence microscopy study. Applied Physics Letters, 2005, 86, 023113.	1.5	43



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127	Microscopic Spatial Distribution of Bound Excitons in High-Quality ZnO. Materials Science Forum, 2005, 483-485, 1065-0.	0.3	0
128	Localization versus field effects in single InGaN quantum wells. Applied Physics Letters, 2004, 84, 58-60.	1.5	36
129	Ostwald ripening and flattening of epitaxial ZnO layers during in situ annealing in metalorganic vapor phase epitaxy. Applied Physics Letters, 2004, 85, 1496-1498.	1.5	39
130	Direct evidence for selective impurity incorporation at the crystal domain boundaries in epitaxial ZnO layers. Applied Physics Letters, 2004, 85, 1976-1978.	1.5	13
131	Self-assembly of ZnO nanowires and the spatial resolved characterization of their luminescence. Nanotechnology, 2004, 15, 1401-1404.	1.3	52
132	Microscopic spatial distribution of bound excitons in high-quality ZnO. Journal of Crystal Growth, 2004, 272, 785-788.	0.7	4
133	Bound exciton and donor-acceptor pair recombinations in ZnO. Physica Status Solidi (B): Basic Research, 2004, 241, 231-260.	0.7	1,499
134	A two-step metal organic vapor phase epitaxy growth method for high-quality ZnO on GaN/Al <sub>2</sub> O <sub>3</sub> (0001). Journal of Crystal Growth, 2004, 267, 140-144.	0.7	52
135	Heteroepitaxy and nitrogen doping of high-quality ZnO. Journal of Crystal Growth, 2004, 272, 800-804.	0.7	16
136	Metalorganic chemical vapor phase deposition of ZnO with different O-precursors. Journal of Crystal Growth, 2003, 248, 14-19.	0.7	46
137	MOVPE growth of GaN on Si(111) substrates. Journal of Crystal Growth, 2003, 248, 556-562.	0.7	125
138	Variation of structural and optical properties across an AlGaN/GaN HEMT structure directly imaged by cathodoluminescence microscopy. Physica Status Solidi A, 2003, 200, 183-186.	1.7	0
139	Metalorganic chemical vapor phase epitaxy of gallium-nitride on silicon. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1583-1606.	0.8	116
140	Gallium-nitride-based devices on silicon. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1940-1949.	0.8	18
141	Optical micro-characterization of group-III-nitrides: correlation of structural, electronic and optical properties. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1795-1815.	0.8	12
142	The origin of the PL photoluminescence Stokes shift in ternary group-III nitrides: field effects and localization. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1835-1845.	0.8	15
143	Optical and structural analysis of ZnCdO layers grown by metalorganic vapor-phase epitaxy. Applied Physics Letters, 2003, 83, 3290-3292.	1.5	174
144	Metal Organic Vapor Phase Epitaxy of ZnO on GaN/Si(111) Using Tertiary-Butanol as O-Precursor. Japanese Journal of Applied Physics, 2003, 42, 7474-7477.	0.8	23

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145	Optical evaluation of pretreated InGaN quantum well structures. Materials Research Society Symposia Proceedings, 2003, 798, 598.	0.1	1
146	Non-planar Selective Area Growth and Characterization of GaN and AlGaIn. Japanese Journal of Applied Physics, 2003, 42, 6276-6283.	0.8	24
147	Microscopic correlation of redshifted luminescence and surface defects in thick In <sub>x</sub> Ga <sub>1-x</sub> N layers. Applied Physics Letters, 2002, 80, 3524-3526.	1.5	21
148	Response to "Comment on "Low Stokes shift in thick and homogeneous InGaIn epilayers" [Appl. Phys. Lett 81, 1353 (2002)]. Applied Physics Letters, 2002, 81, 1355-1356.	1.5	1
149	Low Stokes shift in thick and homogeneous InGaIn epilayers. Applied Physics Letters, 2002, 80, 550-552.	1.5	58
150	High Quality GaN Grown by Facet-Controlled ELO (FACELO) Technique. Physica Status Solidi A, 2002, 194, 545-549.	1.7	18
151	Spatial variation of luminescence of InGaIn alloys measured by highly-spatially-resolved scanning cathodoluminescence. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 93, 19-23.	1.7	10
152	Spatial Variation of Luminescence of InGaIn Alloys Measured by Highly-Spatially-Resolved Scanning Cathodoluminescence. Physica Status Solidi (B): Basic Research, 2001, 228, 35-39.	0.7	10
153	A Comparison of Rutherford Backscattering Spectroscopy and X-Ray Diffraction to Determine the Composition of Thick InGaIn Epilayers. Physica Status Solidi (B): Basic Research, 2001, 228, 41-44.	0.7	23
154	Spatial variation of luminescence in thick GaN films. Applied Physics Letters, 2001, 78, 1222-1224.	1.5	16
155	Comparison of the Mechanism of Optical Amplification in InGaIn/GaN Heterostructures Grown by Molecular Beam Epitaxy and MOCVD. Physica Status Solidi A, 2000, 180, 327-332.	1.7	7
156	Optical and structural characterization of a self-aligned single electron transistor structure by cathodoluminescence microscopy. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 363-366.	1.3	2
157	Exciton dynamics in ZnCdSe/ZnSe ridge quantum wires. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 526-530.	1.3	2
158	Time-resolved micro-photoluminescence of epitaxial laterally overgrown GaN. Journal of Luminescence, 2000, 87-89, 1192-1195.	1.5	3
159	Micro-Raman and cathodoluminescence studies of epitaxial laterally overgrown GaN with tungsten masks: A method to map the free-carrier concentration of thick GaN samples. Applied Physics Letters, 2000, 76, 3418-3420.	1.5	30
160	Comparison of Different Epitaxial Lateral Overgrowth GaN Structures using SiO <sub>2</sub> and Tungsten Mask by Cathodoluminescence Microscopy and Micro-Raman Spectroscopy. Materials Science Forum, 2000, 338-342, 1483-1486.	0.3	0
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